

ESDA6V1L
Dual transil array for ESD protection

Revision:B

General Description

The ESDA6V1L is a dual monolithic voltage suppressor designed to protect components which are connected to data and transmission lines against ESD. It clamps the voltage just above the logic level supply for positive transients and to a diode drop below ground for negative transients. It can also work as bidirectional suppressor by connecting only pin1 and 2.

Applications

- Computers
- Printers
- Communication systems

It is particularly recommended for the RS232 I/O port protection where the line interface withstands only with 2kV ESD surges.

Features

- 2 Unidirectional Transil functions
- Low leakage current: $I_{RM} \max < 1 \mu A$ at V_{RM}
- 300W peak pulse power(8/20 μs)

Complies with the following standards

IEC61000-4-2

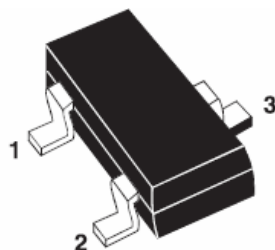
Level 4 15 kV (air discharge)

8 kV(contact discharge)

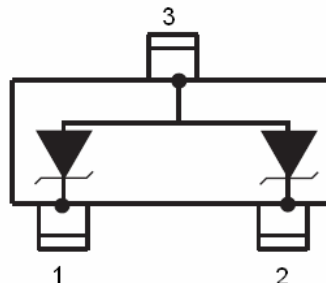
MIL STD 883E - Method 3015-7 Class 3

25 kV HBM (Human Body Model)

Functional diagram



SOT-23

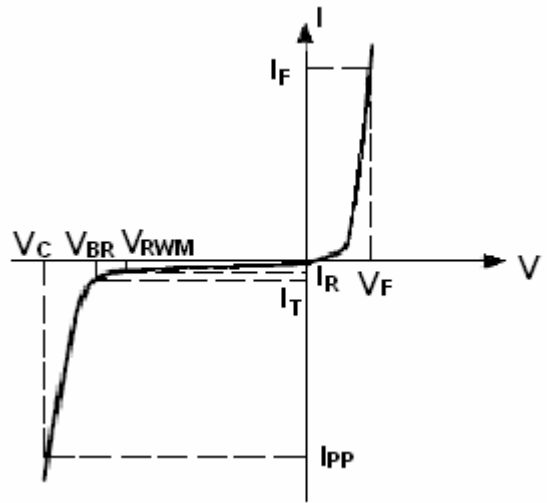


Absolute Ratings ($T_{amb}=25^{\circ}C$)

Symbol	Parameter	Value	Units
P_{PP}	Peak Pulse Power ($t_p = 8/20\mu s$)	300	W
T_L	Maximum lead temperature for soldering during 10s	260	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55 to +155	$^{\circ}C$
T_{op}	Operating Temperature Range	-40 to +125	$^{\circ}C$
T_j	Maximum junction temperature	150	$^{\circ}C$
V_{PP}	Electrostatic discharge		
	MIL STD 883C -Method 3015-6	25	kV
	IEC61000-4-2 air discharge	15	
IEC61000-4-2 contact discharge	8		

Electrical Parameter

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
I_T	Test Current
V_{BR}	Breakdown Voltage @ I_T
I_F	Forward Current
V_F	Forward Voltage @ I_F



Electrical Characteristics

Part Numbers	V_{BR}			I_T	V_{RWM}	I_R	V_F	I_F	C
	Min.	Typ.	Max.				Max.		Typ. 0v bias
	V	V	V				V		pF
ESDA6V1L	6.1	6.7	7.2	1	5.25	20	1.25	200	140

1. Square pulse $I_{PP}=15A, t_p=2.5\mu s$
2. $\Delta V_{BR}=aT*(T_{amb}-25^\circ C)*V_{BR}(25^\circ C)$
3. Capacitance is measured by pin 1 to pin 3 or pin2 to pin 3.

Typical Characteristics

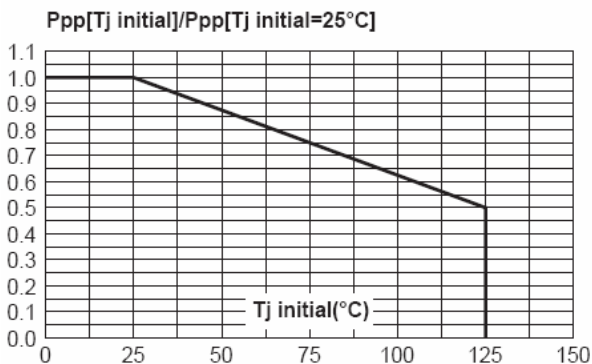


Fig1. Peak power dissipation versus Initial junction temperature

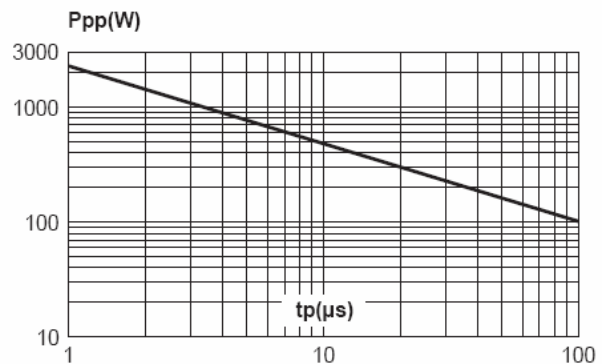


Fig2. Peak pulse power versus exponential pulse duration(T_j initial=25°C)

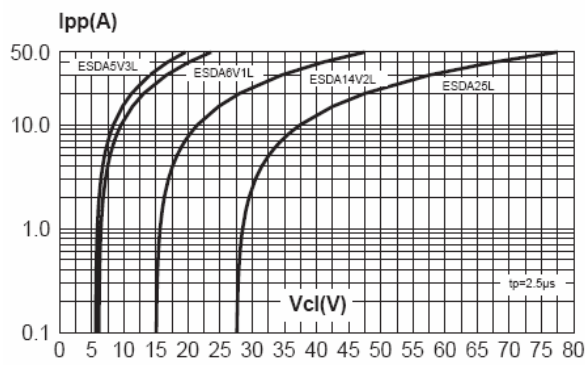


Fig3. Clamping voltage versus peak pulse current (T_j initial=25°C, rectangular Waveform, $t_p=2.5\mu s$)

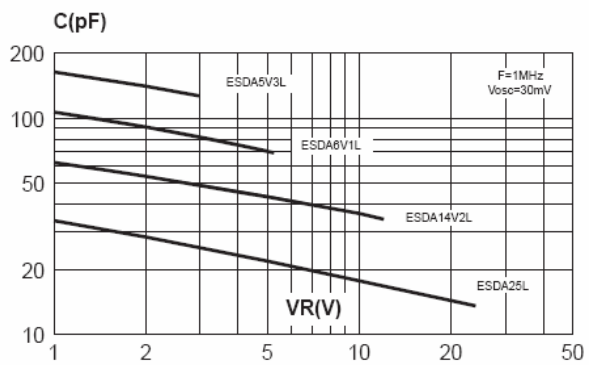


Fig4. Capacitance versus reverse Applied voltage

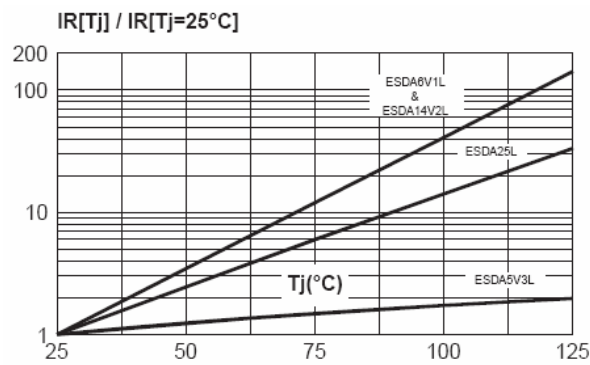


Fig5. Relative variation of leakage current Versus junction temperature

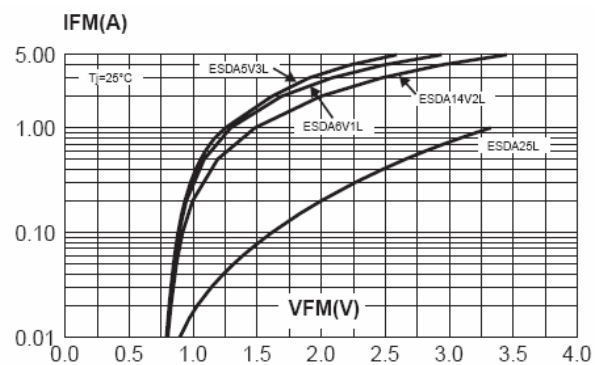


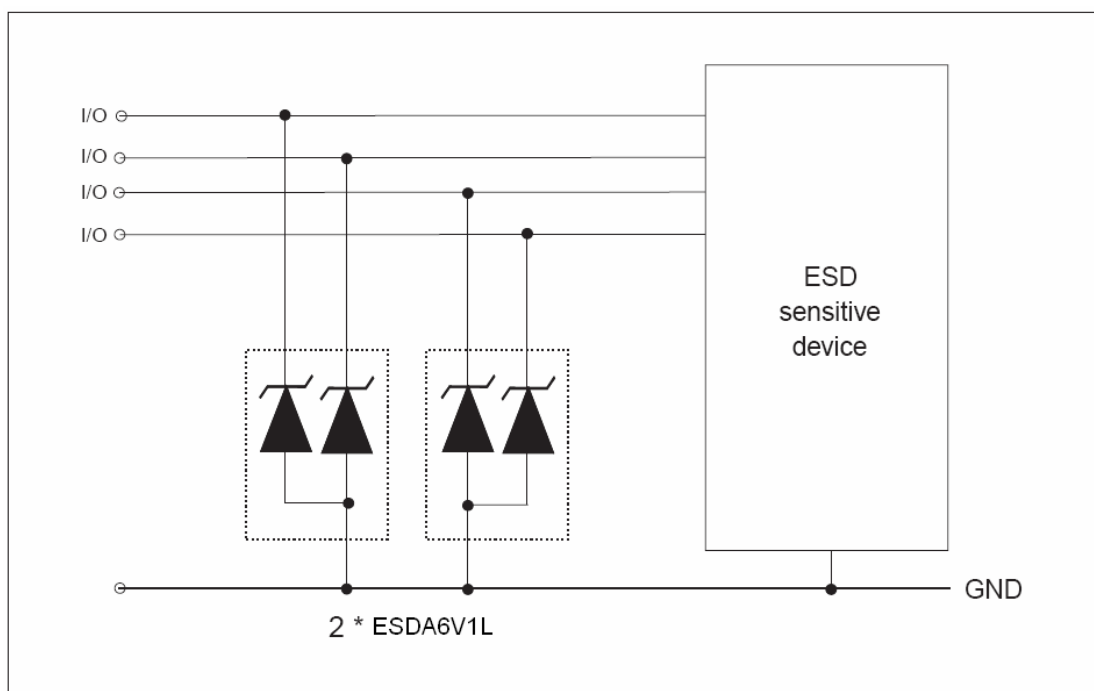
Fig6. Peak forward voltage drop versus peak forward current

Application Note

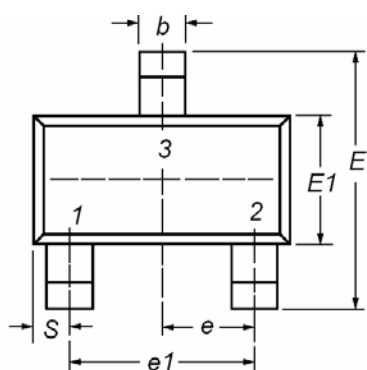
Electrostatic discharge (ESD) is a major cause of failure in electronic systems. Transient Voltage Suppressors (TVS) is an ideal choice for ESD protection. They are capable of clamping the incoming transient to a low enough level such that damage to the protected semiconductor is prevented.

Surface mount TVS arrays offer the best choice for minimal lead inductance. They serve as parallel protection elements, connected between the signal lines to ground. As the transient rises above the operating voltage of the device, the TVS array becomes a low impedance path diverting the transient current to ground. The ESDA6V1L array is the ideal board level protection of ESD sensitive semiconductor components.

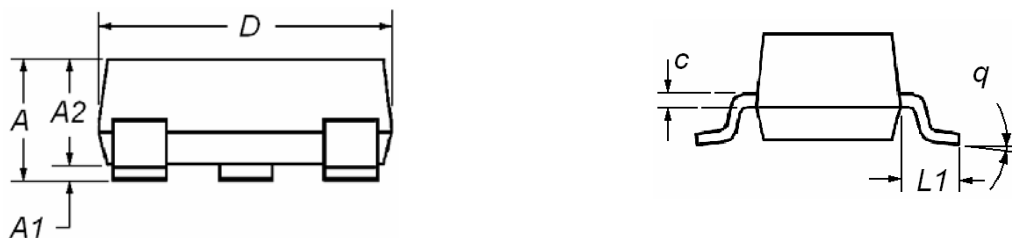
The tiny SOT-23 package allows design flexibility in the design of high density boards where the space saving is at a premium. This enables to shorten the routing and contributes to hardening against ESD.



SOT-23 Mechanical Data



Dim	Millimeters		
	Min	TYP	Max
A	1.00	1.20	1.40
A1	0	0.05	0.10
A2	1.00	1.15	1.30
b	0.35	0.40	0.50
c	0.10	0.15	0.20
D	2.70	2.90	3.10
E	2.40	2.60	2.80
E1	1.40	1.50	1.60
e	0.85	1.00	1.15
e1	1.80	1.90	2.00
L1	0.40	.	
q	0°	5°	10°
S	0.45	0.50	0.55



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